ECOLE POLYTECHNIQUE FEDERALE DE LAUSANNE
CENTRE DE MICRO- NANO- TECHNOLOGIE (CMI)

SILICON TEST WAFERS - SPECIFICATION 100/P/SS/01-100

Rev. 2.1 / 12.04.02

1. Material Parameters

1.1	Growth method	Czochralski
1.2	Conductivity type	P
1.3	Dopant	Boron
1.4	Orientation	<100>
1.5	Off-orientation	0° ± 1.0°
1.6	Resistivity range	0.1 - 100 ohm-cm
1.7	Dislocation density	< 100 / cm^2

2. Dimensional Parameters

2.1	Diameter	100 ± 0.5 mm
2.2	Thickness	525 ± 25 µm
2.3	Primary flat orientation	<110> ± 2°
2.4	Primary flat length	32.5 ± 2.5 mm
2.5	Secondary flat location	90° CW from primary flat
2.6	Secondary flat length	18 ± 2 mm
2.7	Total thickness variation, max	25 µm
2.8	Bow, max	30 µm
2.9	Warp, max	30 µm
2.10	Edge contour	As per SEMI MI-0996
2.11	Wafer ID marking	As specified

3. Front Surface Parameters

3.1	Particules, max	0.1 / cm^2
3.2	Scratches	None
3.3	Haze	None
3.4	Edge chips and indents	None
3.5	Orange peel	None
3.6	Saw marks	None
3.7	Other surface defects	None

4. Back Surface Parameters

4.1	Back surface	Etched
4.2	Edge chips	None
4.3	Saw marks	None